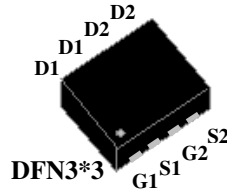
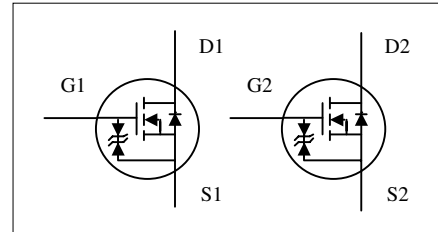
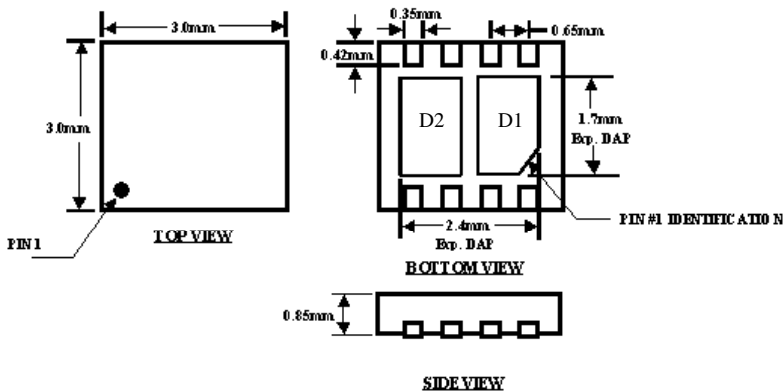




- ▼ Bottom Exposed DFN
- ▼ Low On-resistance
- ▼ Lower Profile



BV_{DSS}	30V
$R_{DS(ON)}$	27m Ω
I_D	5.5A



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 10	V
$I_D@T_A=25^\circ C$	Continuous Drain Current ³	5.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current ³	4.4	A
I_{DM}	Pulsed Drain Current ¹	20	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.25	W
	Linear Derating Factor	0.01	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	100	$^\circ C/W$



N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.02	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =5A	-	-	27	mΩ
		V _{GS} =2.5V, I _D =3A	-	-	33	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.3	-	1.2	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	-	5	-	S
I _{DSS}	Drain-Source Leakage Current (T _j =25°C)	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =24V, V _{GS} =0V	-	-	10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±10V	-	-	±30	uA
Q _g	Total Gate Charge ²	I _D =5A	-	11	18	nC
Q _{gs}	Gate-Source Charge	V _{DS} =25V	-	1.2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	3.8	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	3.5	-	ns
t _r	Rise Time	I _D =1A	-	8.5	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	25	-	ns
t _f	Fall Time	R _D =15Ω	-	4.5	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	545	870	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	110	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	80	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =1A, V _{GS} =0V	-	-	1.3	V
t _{rr}	Reverse Recovery Time ²	I _S =5A, V _{GS} =0V,	-	28	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	21	-	nC

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted FR4 board, t ≤ 5s.

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.

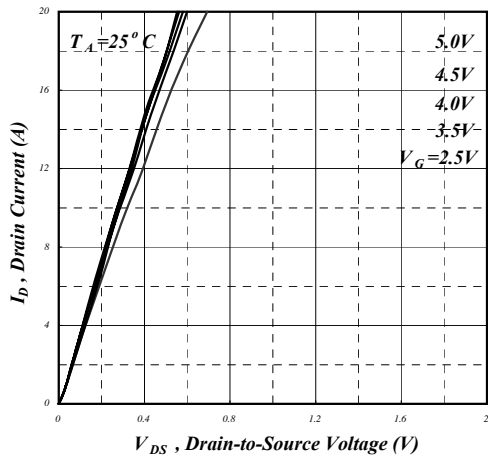


Fig 1. Typical Output Characteristics

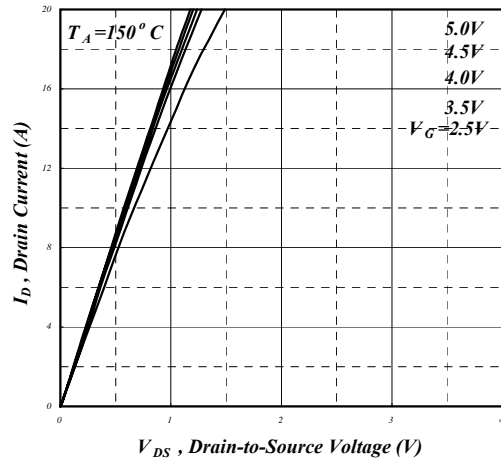


Fig 2. Typical Output Characteristics

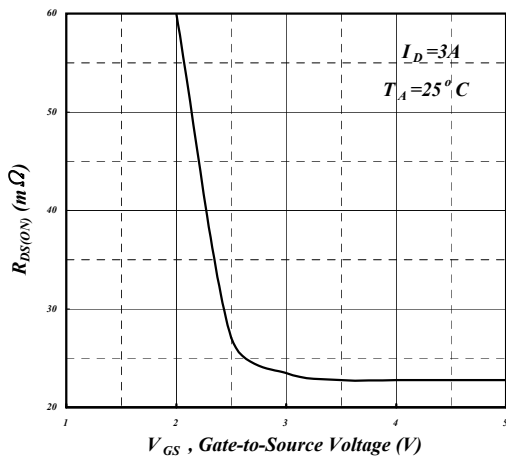


Fig 3. On-Resistance v.s. Gate Voltage

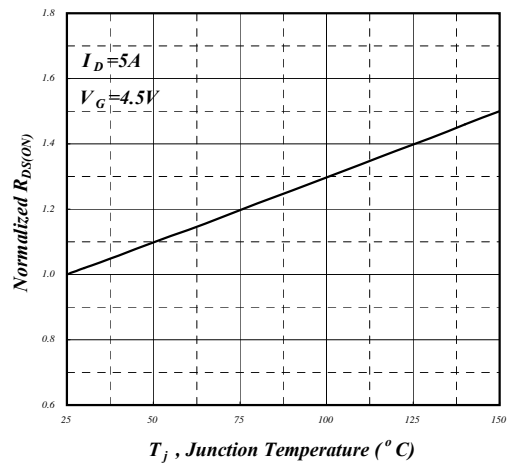


Fig 4. Normalized On-Resistance v.s. Junction Temperature

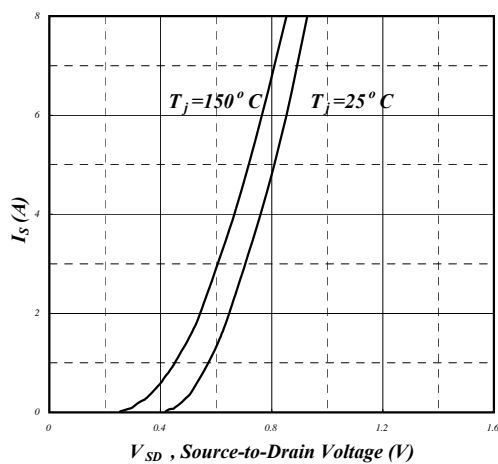


Fig 5. Forward Characteristic of Reverse Diode

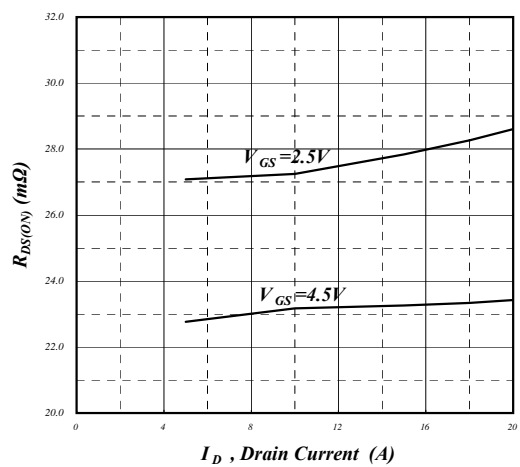


Fig 6. On-Resistance vs. Drain Current

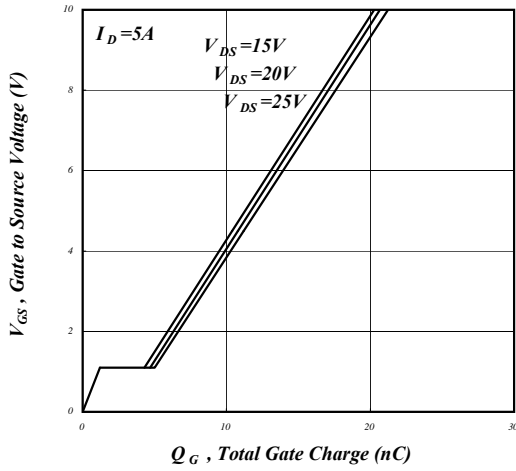


Fig 7. Gate Charge Characteristics

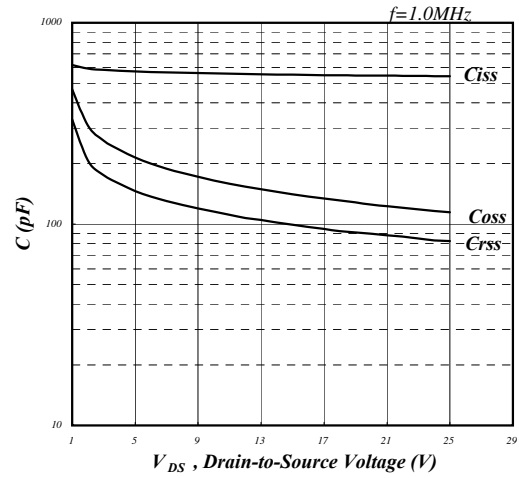


Fig 8. Typical Capacitance Characteristics

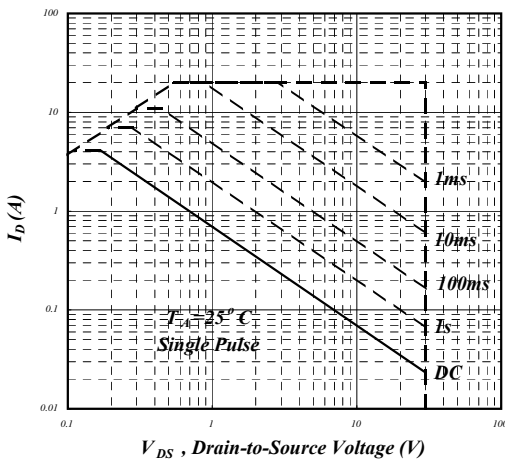


Fig 9. Maximum Safe Operating Area

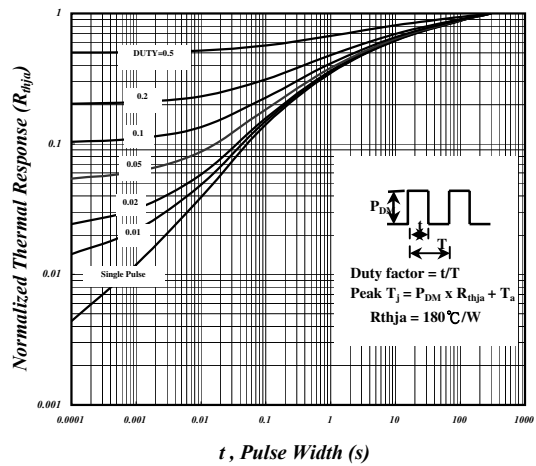


Fig 10. Effective Transient Thermal Impedance

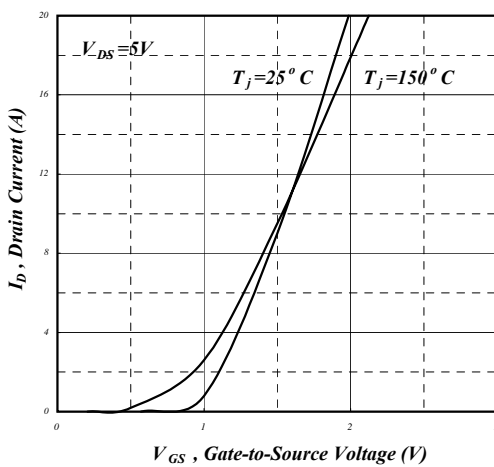


Fig 11. Transfer Characteristics

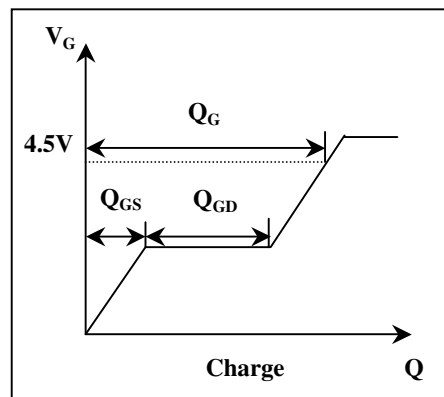
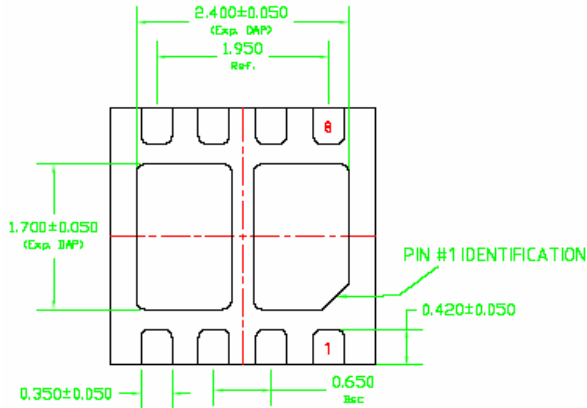


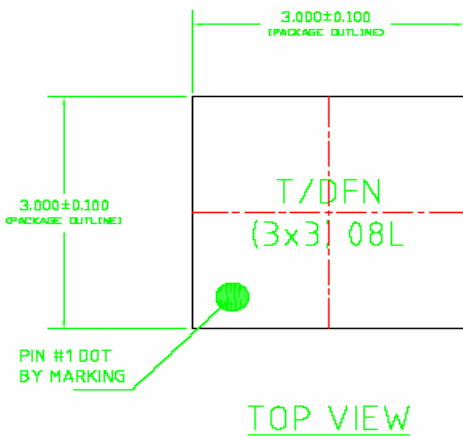
Fig 12. Gate Charge Waveform



Package Outline : T/DFN(3*3)



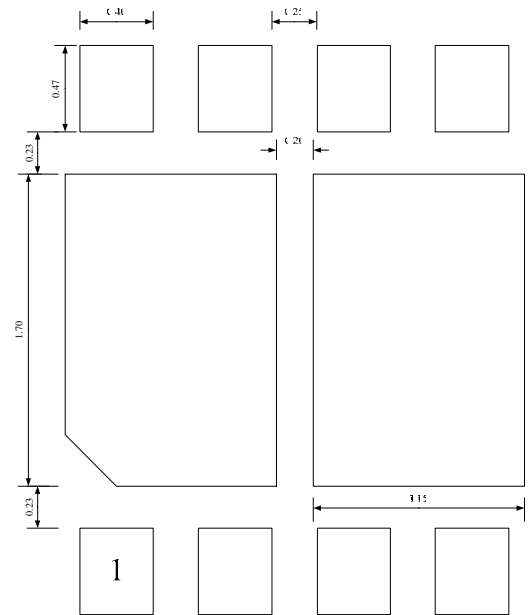
BOTTOM VIEW



TOP VIEW

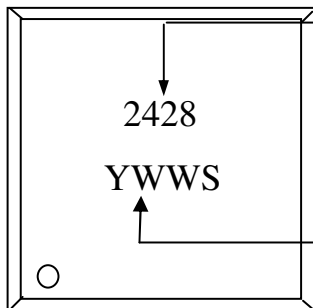
SYMBOLS		Millimeters		
		MIN	NOM	MAX
A	DFN	0.80	0.85	0.90
	TDFN	0.70	0.75	0.80

Foot print



- 1.All Dimension Are In Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.

Part Marking Information & Packing : T/DFN(3*3)



Part Number

Date Code (YWWS)

Y : Last Digit Of The Year

WW : Week

S : Sequence